Contribution ID: **2**
Type: **Standard (20 min including discussion)**

TCAD simulations of LGAD devices [Wednesday!]

Wednesday 2 December 2015 15:50 (20 minutes)

I will present preliminary results from simulated LGAD devices, before and after irradiation.
Electrical properties and response to MIPs and alpha particles will be discussed,
as a function of irradiation fluences, polarization voltage and device temperature.

Summary

I will present preliminary results from simulated LGAD devices, before and after irradiation.

Author: BOMBEN, Marco (Centre National de la Recherche Scientifique (FR))

Co-author: SADROZINSKI, Hartmut (SCIPP, UC santa Cruz)

Presenter: BOMBEN, Marco (Centre National de la Recherche Scientifique (FR))

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